

Product Summary

| BV_{DSS} | $R_{DS(ON)}$ | I_D $T_A = +25^\circ\text{C}$ |
|------------|---------------------------------------|------------------------------------|
| 60V | 8.0m Ω @ $V_{GS} = 10\text{V}$ | 16.5A |

Description and Applications

This MOSFET is designed to meet the stringent requirements of Automotive applications. It is qualified to AEC-Q101, supported by a PPAP and is ideal for use in:

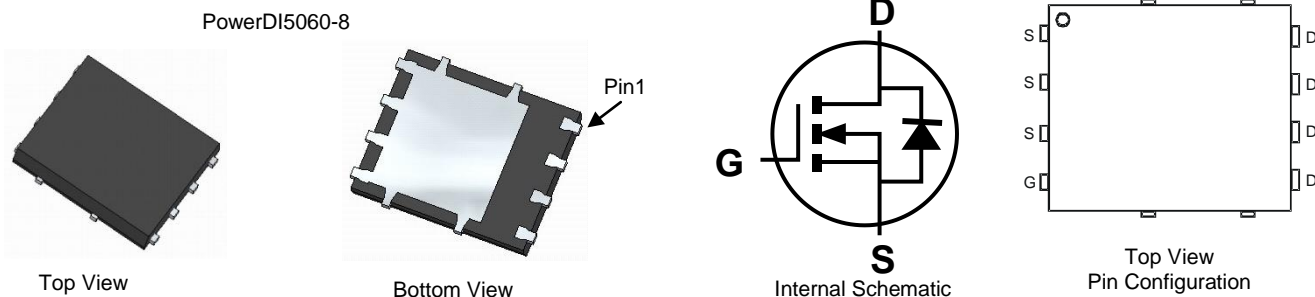
- Motor Control
- DC-DC Converters
- Power Management

Features and Benefits

- Thermally Efficient Package-Cooler Running Applications
- High Conversion Efficiency
- Low $R_{DS(ON)}$ – Minimizes On State Losses
- Low Input Capacitance
- Fast Switching Speed
- <1.1mm Package Profile – Ideal for Thin Applications
- **Lead-Free Finish; RoHS Compliant (Notes 1 & 2)**
- **Halogen and Antimony Free. "Green" Device (Note 3)**
- **Qualified to AEC-Q101 Standards for High Reliability**
- **PPAP Capable (Note 4)**

Mechanical Data

- Case: PowerDI5060-8
- Case Material: Molded Plastic, "Green" Molding Compound.
UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish — Matte Tin Annealed over Copper Leadframe.
Solderable per MIL-STD-202, Method 208 (E3)
- Weight: 0.097 grams (Approximate)

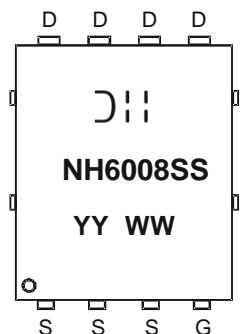


Ordering Information (Note 5)

| Part Number | Case | Packaging |
|-----------------|---------------|---------------------|
| DMNH6008SPSQ-13 | PowerDI5060-8 | 2,500 / Tape & Reel |

- Notes:
1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
 2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
 4. Automotive products are AEC-Q101 qualified and are PPAP capable. Refer to http://www.diodes.com/product_compliance_definitions.html.
 5. For packaging details, go to our website at <http://www.diodes.com/products/packages.html>.

Marking Information



= Manufacturer's Marking
 NH6008SS = Product Type Marking Code
 YYWW = Date Code Marking
 YY = Last Two Digits of Year (ex: 16 = 2016)
 WW = Week Code (01 to 52)

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

| Characteristic | | | Symbol | Value | Unit |
|---|--------------|---|------------------|--------------|------|
| Drain-Source Voltage | | | V _{DSS} | 60 | V |
| Gate-Source Voltage | | | V _{GSS} | ±20 | V |
| Continuous Drain Current (Note 7) V _{GS} = 10V | Steady State | T _A = +25°C T _A = +100°C | I _D | 16.5 11.7 | A |
| | Steady State | T _C = +25°C T _C = +100°C | I _D | 88 63 | A |
| Pulsed Drain Current (380µs Pulse, Duty Cycle = 1%) | | | I _{DM} | 140 | A |
| Maximum Continuous Body Diode Forward Current (Note 7) | | | I _S | 90 | A |
| Avalanche Current (Note 8) L=0.1mH | | | I _{AS} | 62 | A |
| Avalanche Energy (Note 8) L=0.1mH | | | E _{AS} | 194 | mJ |

Thermal Characteristics

| Characteristic | | | Symbol | Value | Unit |
|--|--|--------------|-----------------------------------|-------------|------|
| Total Power Dissipation (Note 6) | | | P _D | 1.6 | W |
| Thermal Resistance, Junction to Ambient (Note 6) | | Steady State | R _{θJA} | 95 | °C/W |
| Total Power Dissipation (Note 7) | | | P _D | 3.3 | W |
| Thermal Resistance, Junction to Ambient (Note 7) | | Steady State | R _{θJA} | 46 | °C/W |
| Thermal Resistance, Junction to Case (Note 7) | | | R _{θJC} | 1.6 | |
| Operating and Storage Temperature Range | | | T _J , T _{STG} | -55 to +175 | °C |

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

| Characteristic | Symbol | Min | Typ | Max | Unit | Test Condition |
|--|---------------------|-----|------|------|------|--|
| OFF CHARACTERISTICS (Note 9) | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 60 | — | — | V | V _{GS} = 0V, I _D = 250µA |
| Zero Gate Voltage Drain Current | I _{DSS} | — | — | 1 | µA | V _{DS} = 48V, V _{GS} = 0V |
| Gate-Source Leakage | I _{GSS} | — | — | ±100 | nA | V _{GS} = ±16V, V _{DS} = 0V |
| ON CHARACTERISTICS (Note 9) | | | | | | |
| Gate Threshold Voltage | V _{GS(TH)} | 2 | — | 4 | V | V _{DS} = V _{GS} , I _D = 250µA |
| Static Drain-Source On-Resistance | R _{DS(ON)} | — | 6.0 | 8.0 | mΩ | V _{GS} = 10V, I _D = 20A |
| Diode Forward Voltage | V _{SD} | — | — | 1.2 | V | V _{GS} = 0V, I _S = 1A |
| DYNAMIC CHARACTERISTICS (Note 10) | | | | | | |
| Input Capacitance | C _{ISS} | — | 2597 | — | pF | V _{DS} = 30V, V _{GS} = 0V f = 1.0MHz |
| Output Capacitance | C _{OSS} | — | 437 | — | | |
| Reverse Transfer Capacitance | C _{rss} | — | 118 | — | | |
| Gate Resistance | R _g | — | 2.0 | — | Ω | V _{DS} = 0V, V _{GS} = 0V, f = 1.0MHz |
| Total Gate Charge (V _{GS} = 10V) | Q _g | — | 40.1 | — | nC | V _{DD} = 30V, I _D = 20A |
| Total Gate Charge (V _{GS} = 4.5V) | Q _g | — | 21.2 | — | | |
| Gate-Source Charge | Q _{gs} | — | 8.3 | — | | |
| Gate-Drain Charge | Q _{gd} | — | 11.8 | — | | |
| Turn-On Delay Time | t _{D(ON)} | — | 5.7 | — | ns | V _{DD} = 30V, V _{GS} = 10V, R _g = 1Ω, I _D = 20A |
| Turn-On Rise Time | t _r | — | 5.0 | — | | |
| Turn-Off Delay Time | t _{D(OFF)} | — | 15.6 | — | | |
| Turn-Off Fall Time | t _f | — | 3.3 | — | | |
| Reverse Recovery Time | t _{RR} | — | 33 | — | ns | I _F = 20A, di/dt = 100A/µs |
| Reverse Recovery Charge | Q _{RR} | — | 33 | — | nC | |

- Notes:
- Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
 - Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
 - I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
 - Short duration pulse test used to minimize self-heating effect.
 - Guaranteed by design. Not subject to product testing.

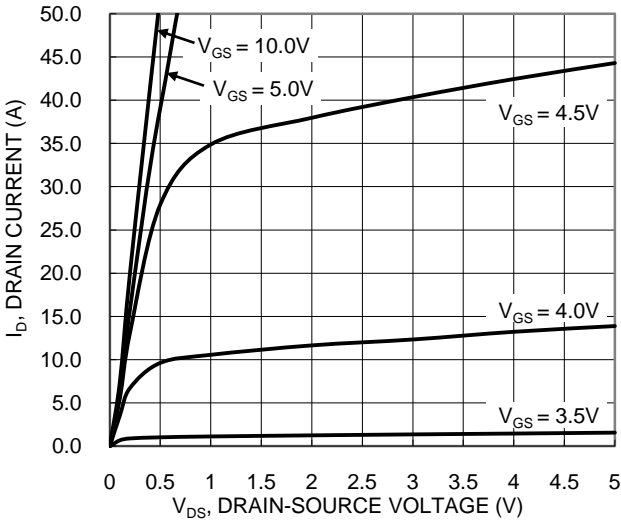


Figure 1. Typical Output Characteristic

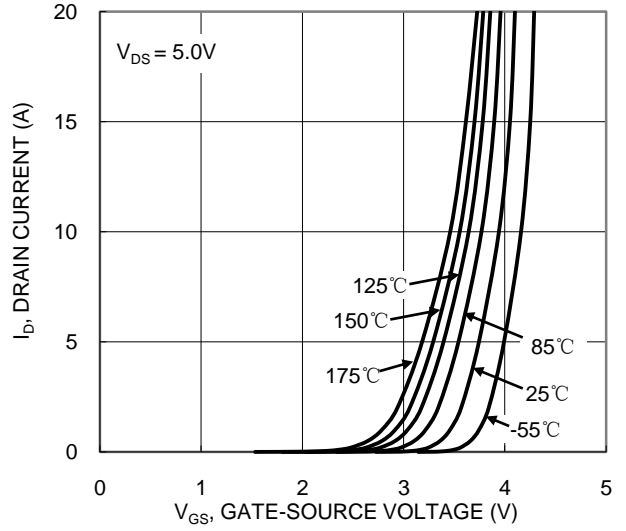


Figure 2. Typical Transfer Characteristic

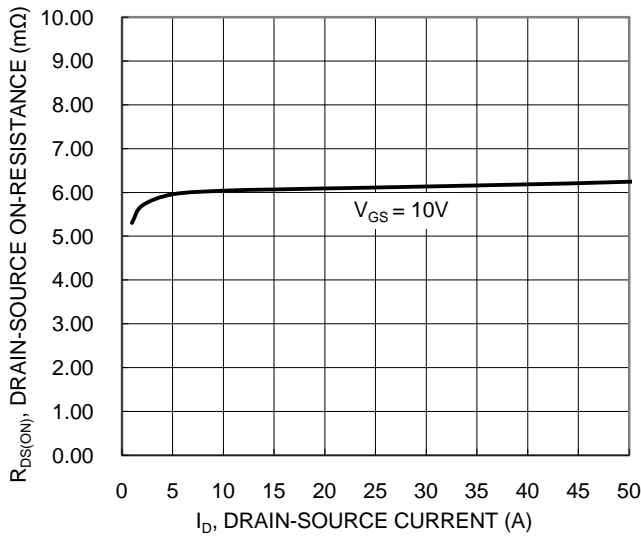


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

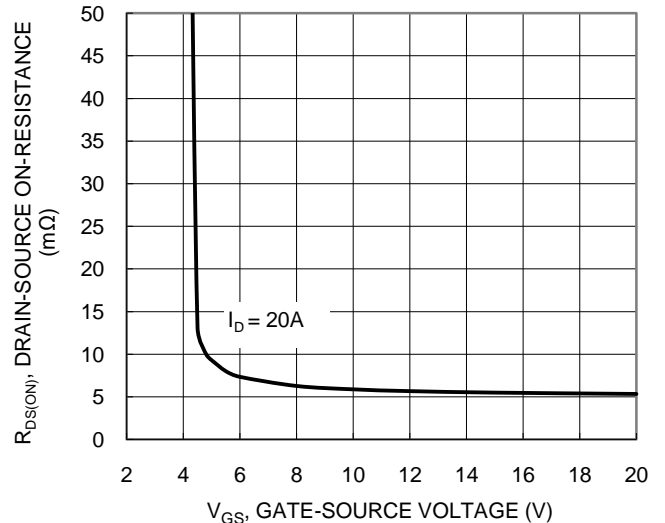


Figure 4. Typical Transfer Characteristic

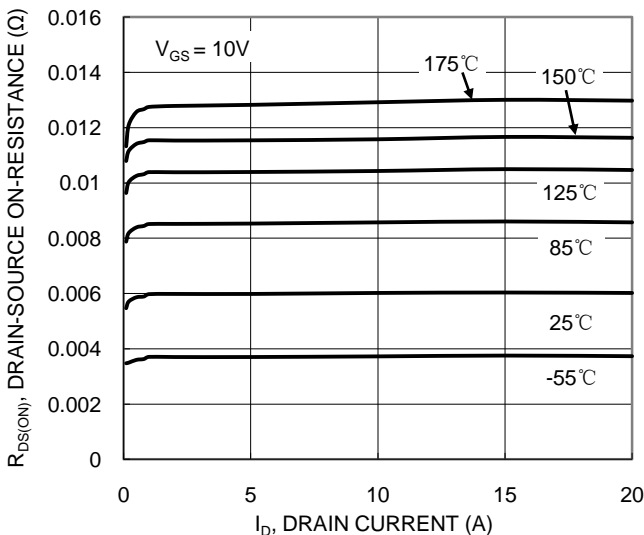


Figure 5. Typical On-Resistance vs. Drain Current and Temperature

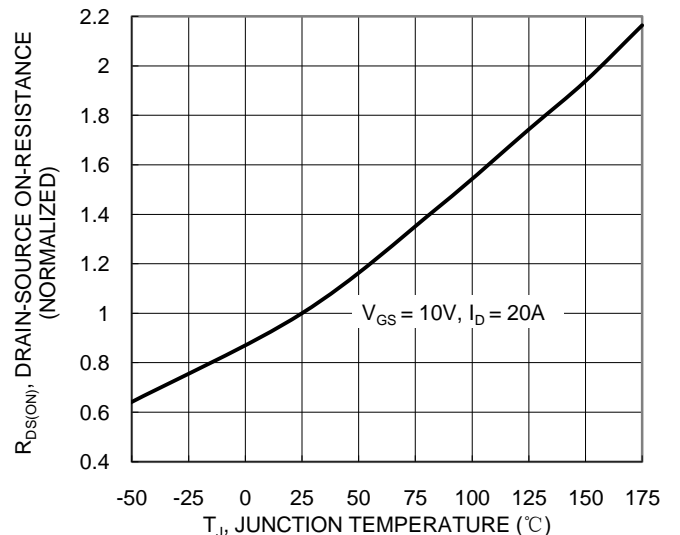


Figure 6. On-Resistance Variation with Temperature

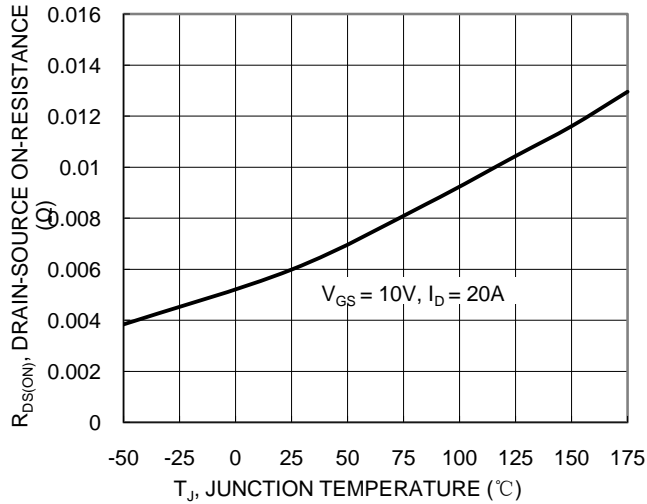


Figure 7. On-Resistance Variation with Temperature

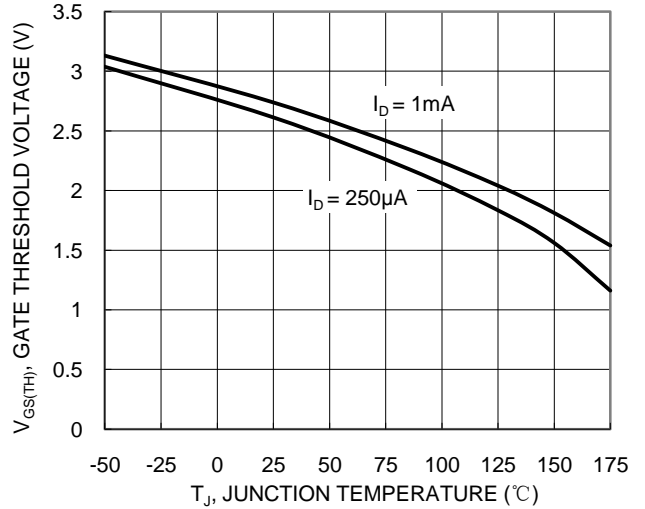


Figure 8. Gate Threshold Variation vs. Temperature

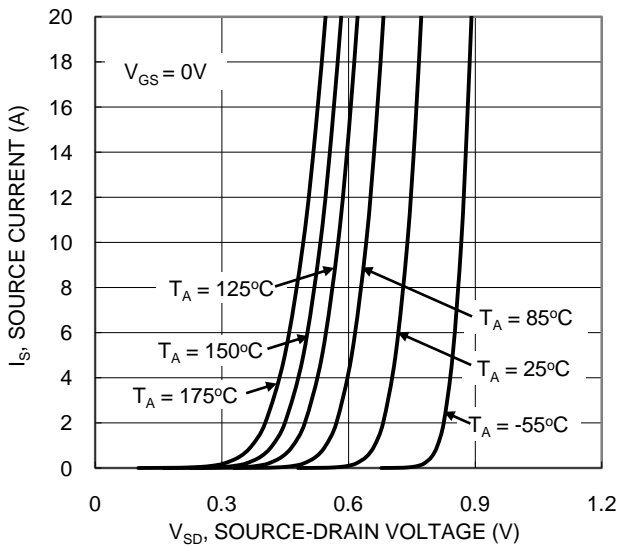


Figure 9. Diode Forward Voltage vs. Current

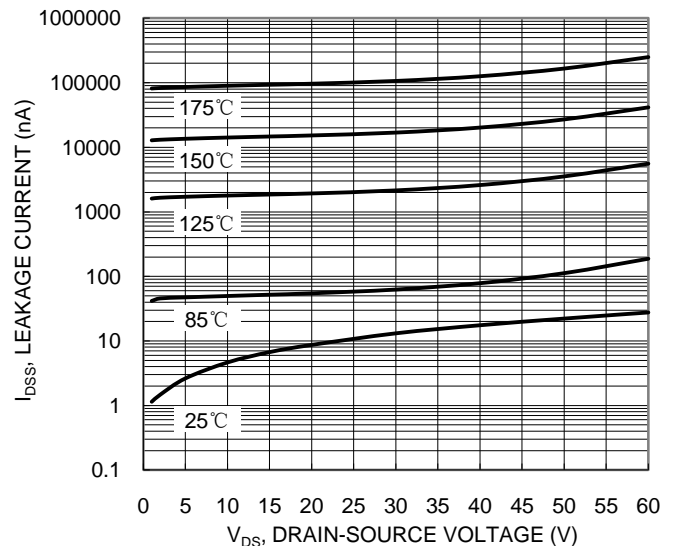


Figure 10. Typical Drain-Source Leakage Current vs. Voltage

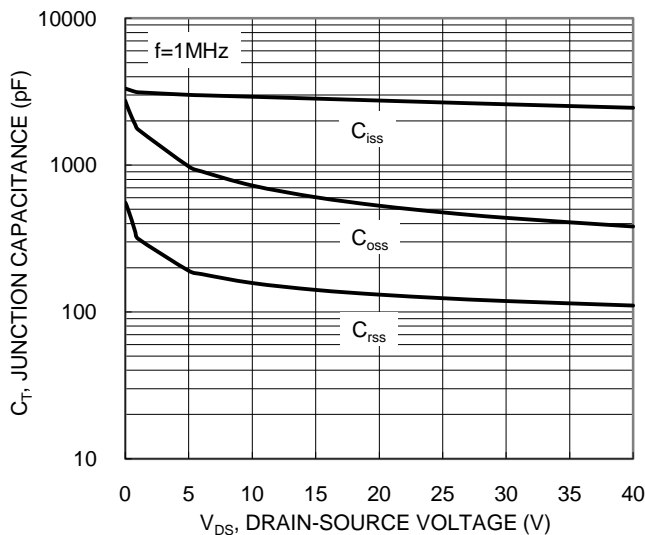


Figure 11. Typical Junction Capacitance

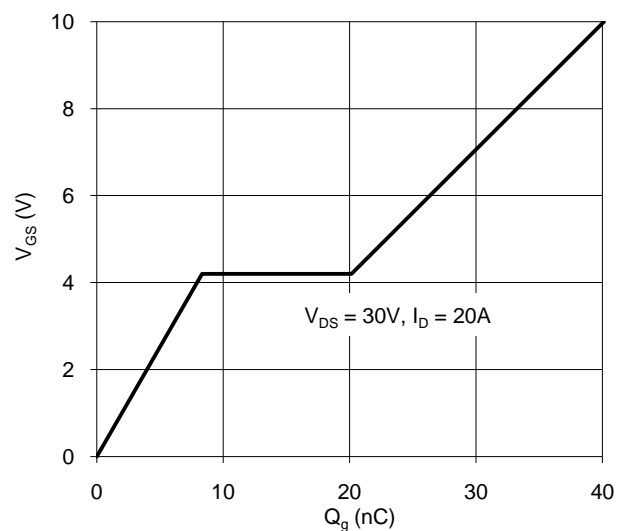
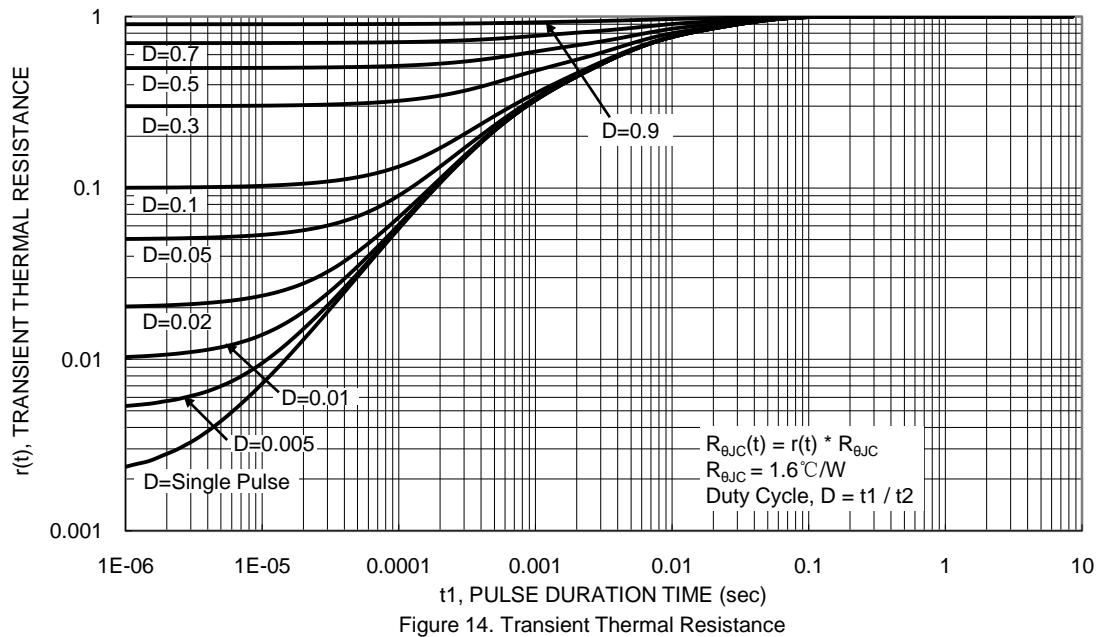
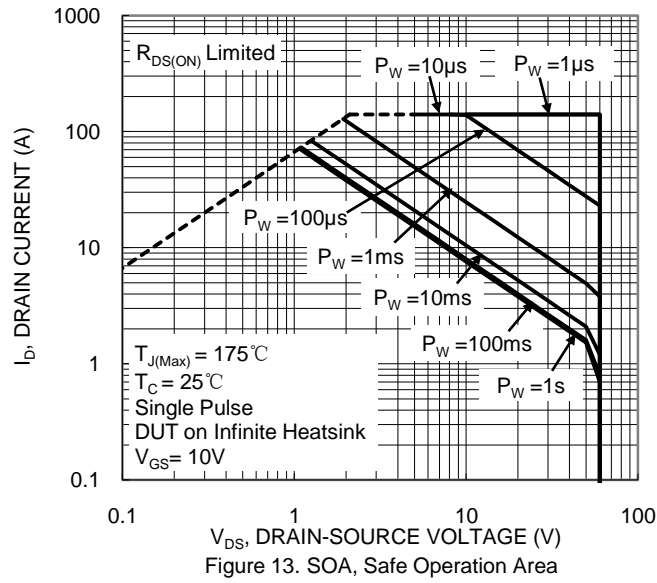


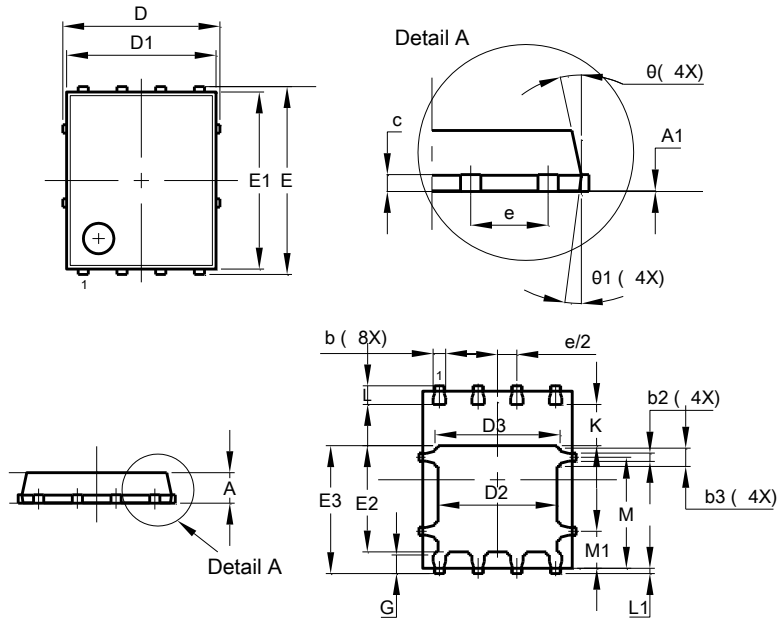
Figure 12. Gate Charge



Package Outline Dimensions

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8

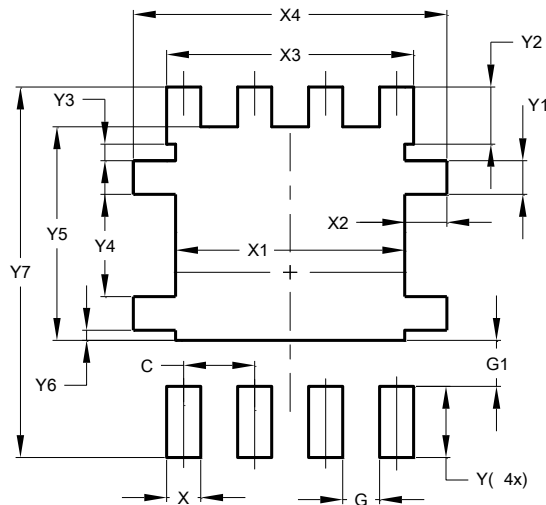


| PowerDI5060-8 | | | |
|----------------------|----------|-------|-------|
| Dim | Min | Max | Typ |
| A | 0.90 | 1.10 | 1.00 |
| A1 | 0.00 | 0.05 | - |
| b | 0.33 | 0.51 | 0.41 |
| b2 | 0.200 | 0.350 | 0.273 |
| b3 | 0.40 | 0.80 | 0.60 |
| c | 0.230 | 0.330 | 0.277 |
| D | 5.15 BSC | | |
| D1 | 4.70 | 5.10 | 4.90 |
| D2 | 3.70 | 4.10 | 3.90 |
| D3 | 3.90 | 4.30 | 4.10 |
| E | 6.15 BSC | | |
| E1 | 5.60 | 6.00 | 5.80 |
| E2 | 3.28 | 3.68 | 3.48 |
| E3 | 3.99 | 4.39 | 4.19 |
| e | 1.27 BSC | | |
| G | 0.51 | 0.71 | 0.61 |
| K | 0.51 | - | - |
| L | 0.51 | 0.71 | 0.61 |
| L1 | 0.100 | 0.200 | 0.175 |
| M | 3.235 | 4.035 | 3.635 |
| M1 | 1.00 | 1.40 | 1.21 |
| θ | 10° | 12° | 11° |
| θ_1 | 6° | 8° | 7° |
| All Dimensions in mm | | | |

Suggested Pad Layout

Please see <http://www.diodes.com/package-outlines.html> for the latest version.

PowerDI5060-8



| Dimensions | Value (in mm) |
|------------|---------------|
| C | 1.270 |
| G | 0.660 |
| G1 | 0.820 |
| X | 0.610 |
| X1 | 4.100 |
| X2 | 0.755 |
| X3 | 4.420 |
| X4 | 5.610 |
| Y | 1.270 |
| Y1 | 0.600 |
| Y2 | 1.020 |
| Y3 | 0.295 |
| Y4 | 1.825 |
| Y5 | 3.810 |
| Y6 | 0.180 |
| Y7 | 6.610 |

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